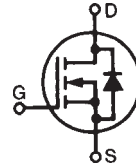


# MegaMOS™ FET

IXTH / IXTM 67N10  
IXTH / IXTM 75N10  
IXTT 75N10

V <sub>DSS</sub>	I <sub>D25</sub>	R <sub>DS(on)</sub>
100 V	67 A	25 mΩ
100 V	75 A	20 mΩ

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	100	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	100	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	67N10 75N10	67 75 A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	67N10 75N10	268 300 A
P <sub>D</sub>	T <sub>C</sub> = 25°C	300	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
M <sub>d</sub>	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204	18 g
		TO-247	6 g
		TO-268	5 g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		10	°C

TO-247 AD (IXTH)

TO-204 AE (IXTM)

TO-268 (IXTT)

G = Gate, D = Drain,  
S = Source, TAB = Drain

### Features

- International standard packages
- Low R<sub>DS(on)</sub> HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

### Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4 mA	2.0		V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = 0.8 • V <sub>DSS</sub> V <sub>GS</sub> = 0 V	T <sub>J</sub> = 25°C		250 μA
		T <sub>J</sub> = 125°C		1 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	67N10		0.025 Ω
		75N10		0.020 Ω

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = I_{D25}$ , pulse test	25	30	S	
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF	
$C_{oss}$			1300	pF	
$C_{rss}$			550	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ , (External)		40	60	ns
$t_r$			60	110	ns
$t_{d(off)}$			100	140	ns
$t_f$			30	60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		180	260	nC
$Q_{gs}$			30	70	nC
$Q_{gd}$			90	160	nC
$R_{thJC}$	(TO-204, TO-247)			0.42	K/W
$R_{thCK}$			0.25		K/W

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$I_S$	$V_{GS} = 0\text{ V}$	67N10 75N10		67 75	A A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	67N10 75N10		268 300	A A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.75	V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		200		ns

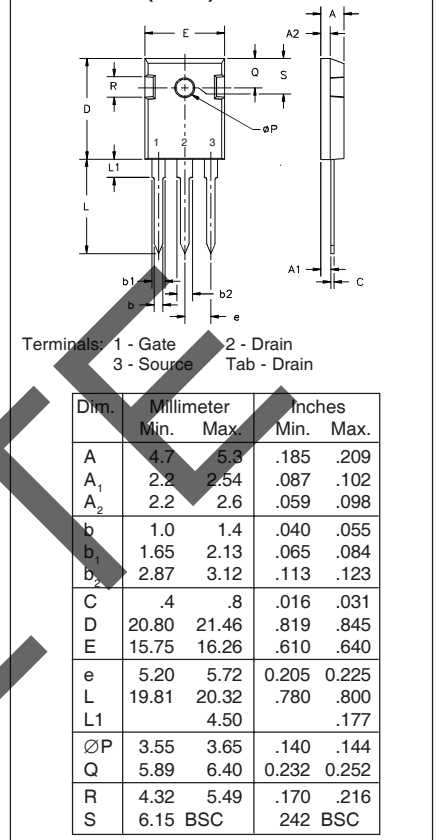
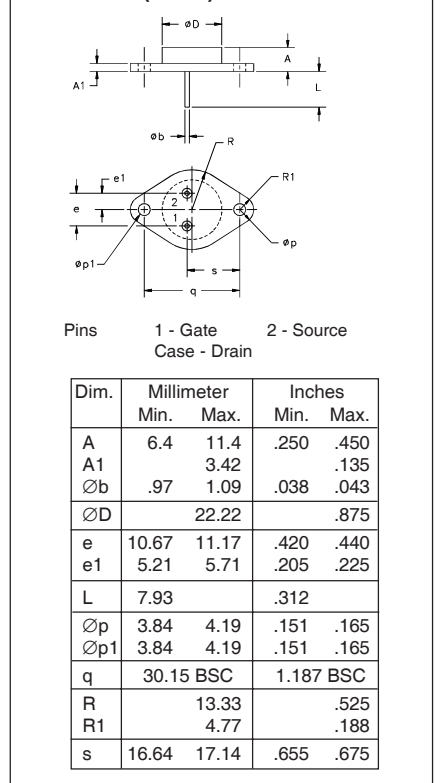
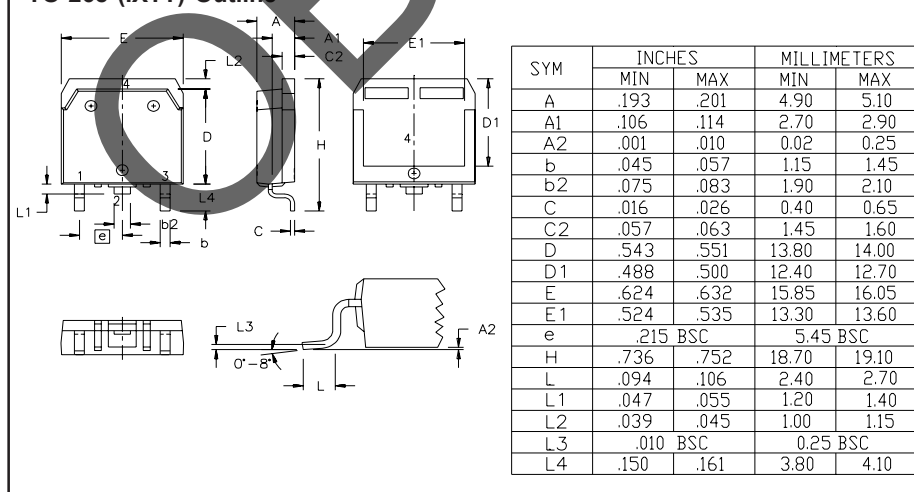
**TO-247 AD (IXTH) Outline**

**TO-204AE (IXTM) Outline**

**TO-268 (IXTT) Outline**


Fig. 1 Output Characteristics

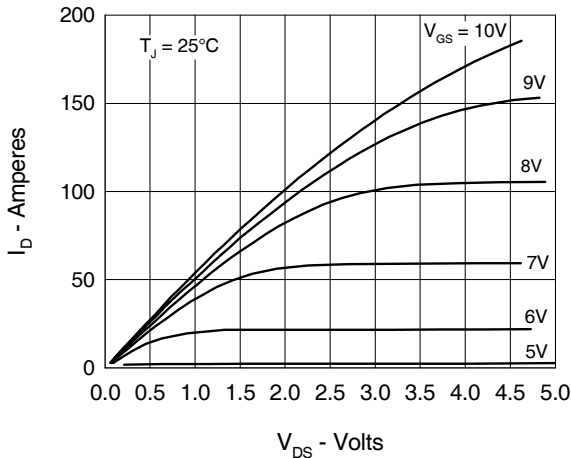


Fig. 2 Input Admittance

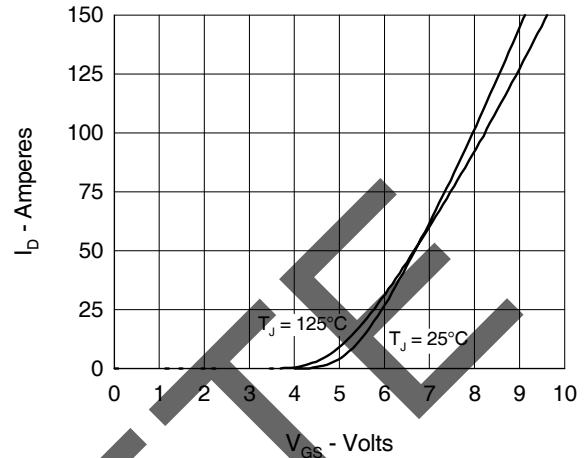


Fig. 3  $R_{DS(on)}$  vs. Drain Current

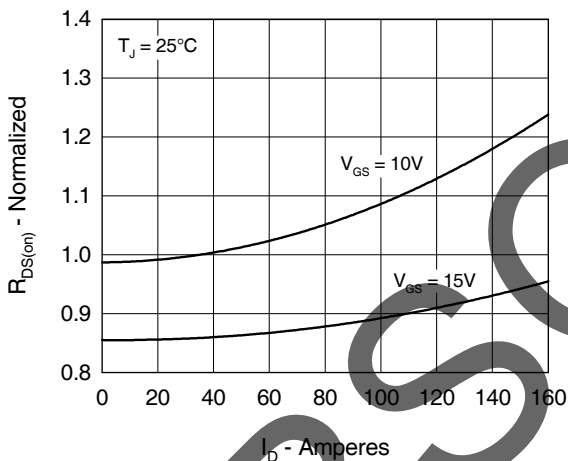


Fig. 4 Temperature Dependence of Drain to Source Resistance

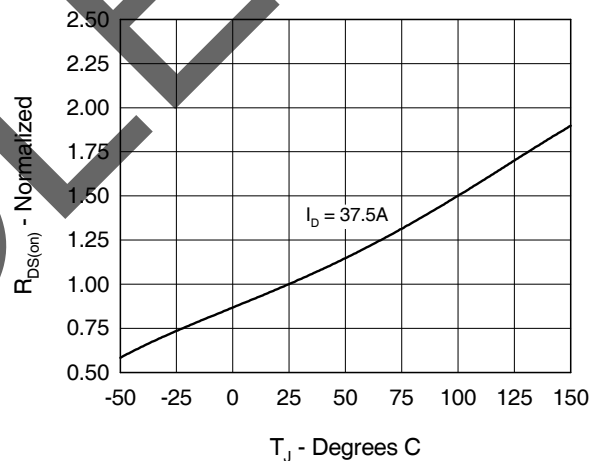


Fig. 5 Drain Current vs. Case Temperature

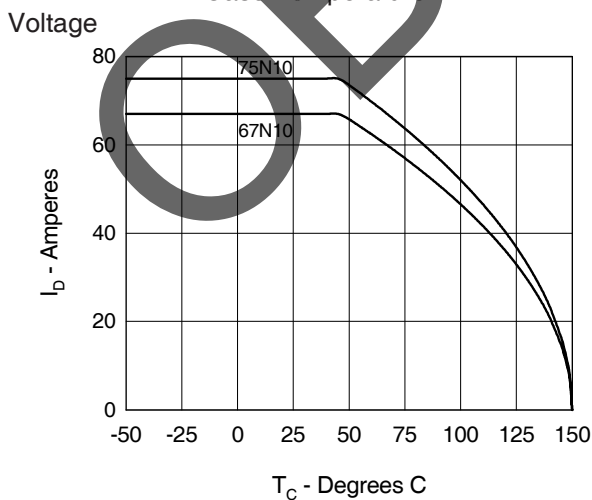
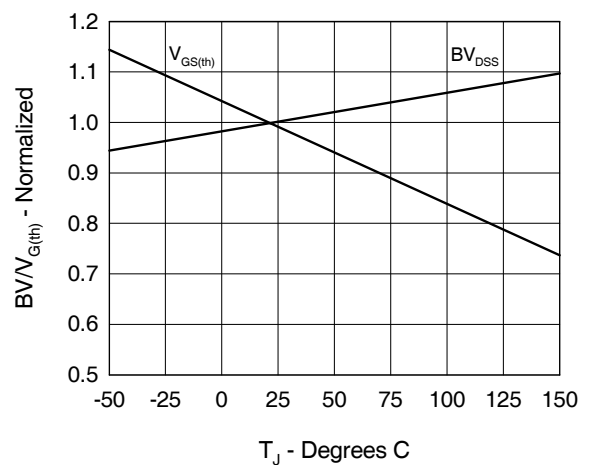
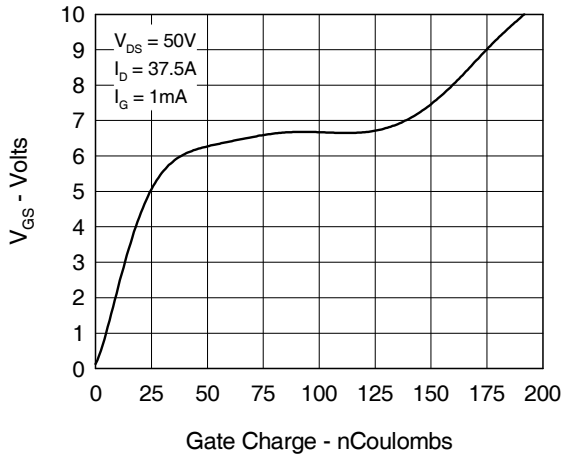


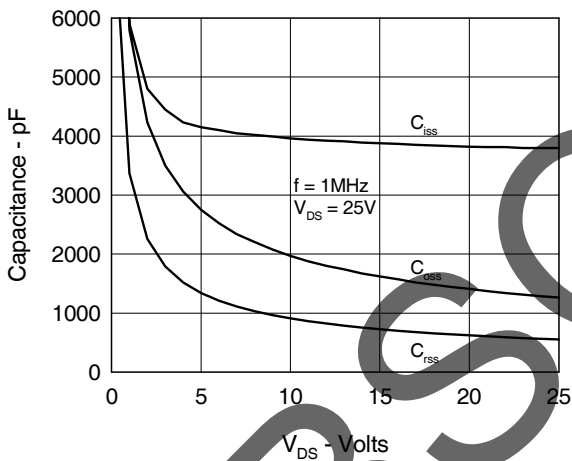
Fig. 6 Temperature Dependence of Breakdown and Threshold



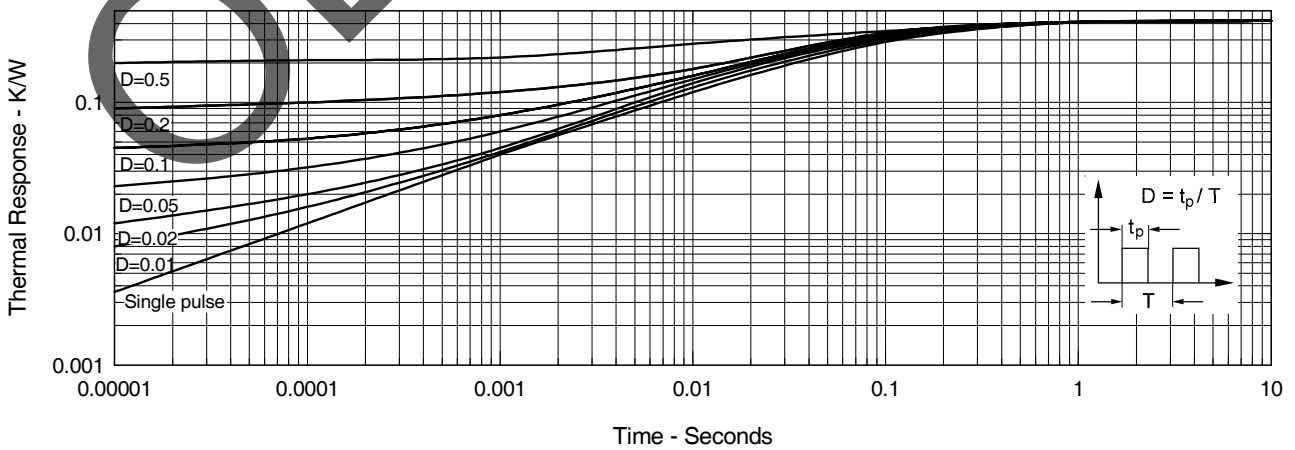
**Fig.7 Gate Charge Characteristic Curve**



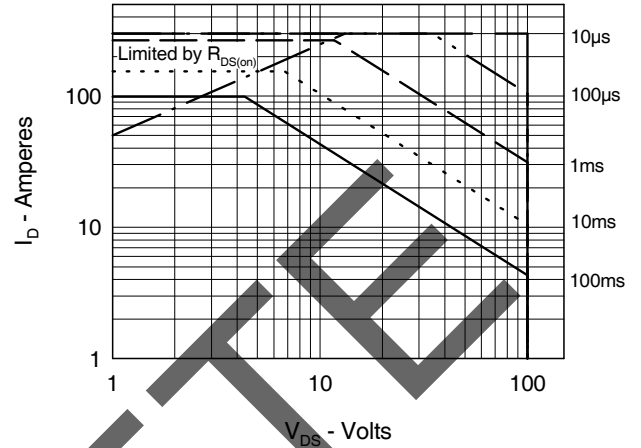
**Fig.9 Capacitance Curves**



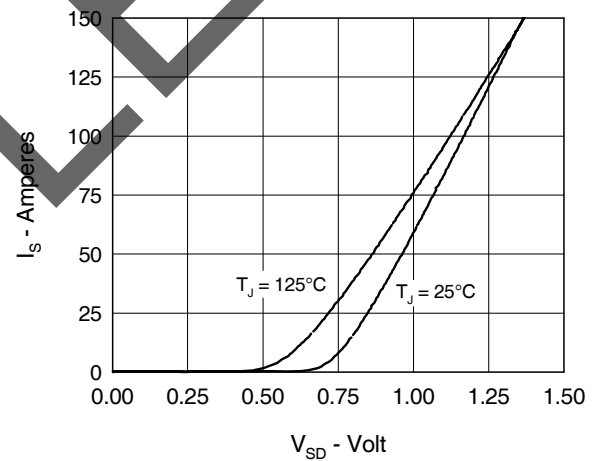
**Fig.11 Transient Thermal Impedance**



**Fig.8 Forward Bias Safe Operating Area**



**Fig.10 Source Current vs. Source to Drain Voltage**





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